

EH29 25 ET T TS -6.144M

Series —
RoHS Compliant (Pb-free) 1.8V 4 Pad 5mm x 7mm
Ceramic SMD LVCMOS Oscillator

Frequency Tolerance/Stability — ±25ppm Maximum

Operating Temperature Range – -40°C to +85°C Nominal Frequency 6.144MHz Pin 1 Connection Tri-State (High Impedance)

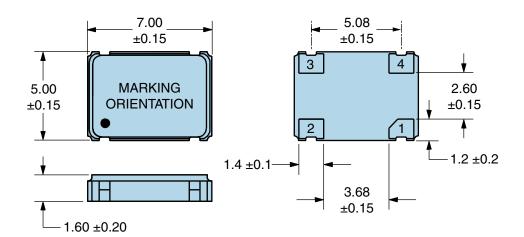
- Duty Cycle 50 ±5(%)

Operating Ter 260°C Reflow #5ppm/Year More at 25°C #5ppm/Year At 25°C #5ppm/Y	
Operating Ter 260°C Reflow #5ppm/Year More rating Temperature Range #5ppm/Year Range	nperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°, Shock, and Vibration) laximum
perating Temperature Range -40°C to +85° 1.8Vdc ±5% put Current 3.5mA Maxim utput Voltage Logic High (Voh) 90% of Vdd M utput Voltage Logic Low (Vol) 10% of Vdd M se/Fall Time 6nSec Maxim uty Cycle 50 ±5(%) (Me pad Drive Capability 15pF Maximu utput Logic Type n 1 Connection i-State Input Voltage (Vih and Vil) 90% of Vdd M	
put Current 3.5mA Maxim utput Voltage Logic High (Voh) 90% of Vdd M utput Voltage Logic Low (Vol) 10% of Vdd M se/Fall Time 6nSec Maxim uty Cycle 50 ±5(%) (Me pad Drive Capability 15pF Maximu utput Logic Type CMOS n 1 Connection Tri-State (High i-State Input Voltage (Vih and Vil) 1.8Vdc ±5% 6nSec ±5% 6n Vdd M 5n ±5(%) (Me 5nd Drive Capability 15pF Maximu 15pF	
put Current 3.5mA Maxim utput Voltage Logic High (Voh) 40 putput Voltage Logic Low (Vol) 50 per Fall Time 60 per Fal	All Locally
utput Voltage Logic High (Voh) utput Voltage Logic Low (Vol) se/Fall Time finSec Maxim fonSec Ma	(Al- L I)
utput Voltage Logic Low (Vol) se/Fall Time 6nSec Maxim uty Cycle 50 ±5(%) (Me pad Drive Capability 15pF Maximu utput Logic Type CMOS n 1 Connection Tri-State (High	ım (No Load)
se/Fall Time 6nSec Maxim Lity Cycle 50 ±5(%) (Me Lity Capability 15pF Maximu Litput Logic Type CMOS Tri-State (High Literature (Vih and Vil) 15pF Maximu 15pF Maxi	nimum (IOH = -8mA)
ty Cycle 50 ±5(%) (Me oad Drive Capability 15pF Maximu utput Logic Type CMOS Tri-State (High i-State Input Voltage (Vih and Vil) 90% of Vdd M	aximum (IOL = +8mA)
pad Drive Capability utput Logic Type CMOS n 1 Connection i-State Input Voltage (Vih and Vil) 75 TipF Maximu CMOS Tri-State (High	ım (Measured at 20% to 80% of waveform)
utput Logic Type CMOS n 1 Connection Tri-State (High i-State Input Voltage (Vih and Vil) 90% of Vdd M	sured at 50% of waveform)
n 1 Connection Tri-State (High i-State Input Voltage (Vih and Vil) 90% of Vdd M	n
i-State Input Voltage (Vih and Vil) 90% of Vdd M	
	Impedance)
	nimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High
andby Current 10µA Maximu	
psolute Clock Jitter ±100pSec Ma	n (Pin 1 = Ground)
art Up Time 10mSec Maxi	
orage Temperature Range -55°C to +125	kimum

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS		
ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Flammability	UL94-V0	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-883, Method 2002, Condition B	
Moisture Resistance	MIL-STD-883, Method 1004	
Moisture Sensitivity	J-STD-020, MSL 1	
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010, Condition B	
Vibration	MIL-STD-883, Method 2007, Condition A	



MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
2	Case Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	6.144M
3	XXXXXX XXXXXX=Ecliptek Manufacturing Identifier

Suggested Solder Pad Layout

All Dimensions in Millimeters



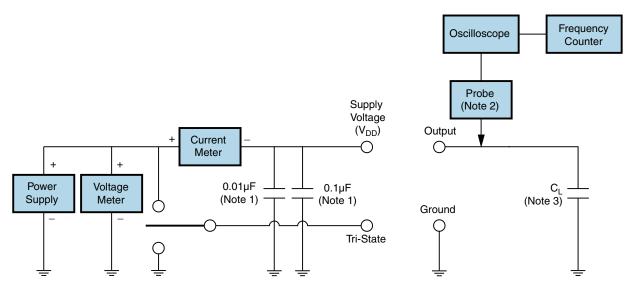
All Tolerances are ±0.1



OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



- Note 1: An external 0.01µF ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.
- Note 3: Capacitance value C₁ includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

<u> </u>	
T _s MAX to T _∟ (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (Ts MIN)	150°C
- Temperature Typical (T _s TYP)	175°C
- Temperature Maximum (T _s MAX)	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T _L to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (tp)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

T _S MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
- Temperature Typical (T _S TYP)	150°C
- Temperature Maximum (T _s MAX)	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T _L to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (tp)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)